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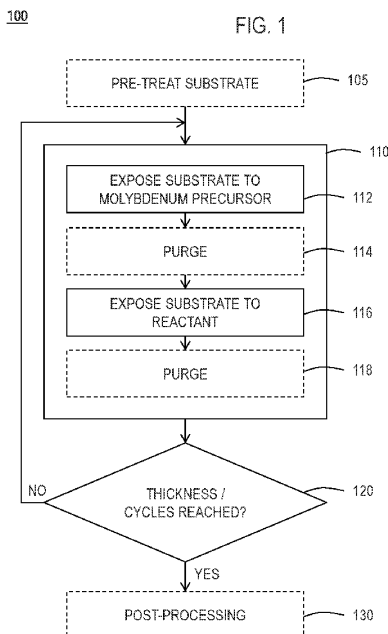
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(54) Title: MOLYBDENUM(0) PRECURSORS FOR DEPOSITION OF MOLYBDENUM FILMS



(57) Abstract: Molybdenum(0) precursors and methods of forming molybdenum-containing films on a substrate surface are described. The molybdenum(0) precursors have a purity of greater than or equal to 90% molybdenum (Mo) on a molar basis. The substrate is exposed to a molybdenum(0) precursor and a reactant to form a molybdenum-containing film having greater than or equal to 80 % molybdenum (Mo) on an atomic basis. In some embodiments, the molybdenum-containing film has greater than or equal to 80 % molybdenum (Mo) on a molar basis. The exposures can be sequential or simultaneous.

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